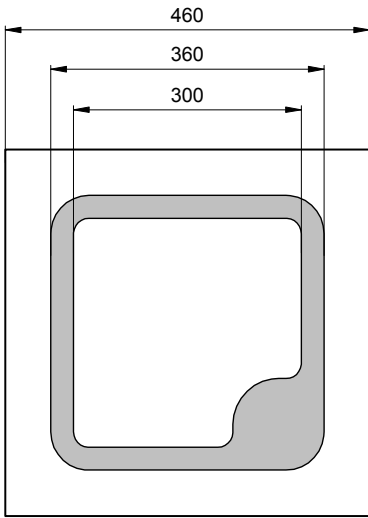


Radiation	Type	Technology	Electrodes
Infrared	MQW	InGaAs/GaAs	N (cathode) up

 <p style="text-align: center;">PD-02</p>	typ. dimensions (μm)	
	typ. thickness 260 (±20) μm <u>cathode</u> gold alloy, 1.5 μm <u>anode</u> gold alloy, 1.5 μm, solderable	

Optical and Electrical Characteristics

$T_{amb} = 25^{\circ}\text{C}$, unless otherwise specified

Parameter	Test conditions	Symbol	Min	Typ	Max	Unit
Forward voltage	$I_F = 100 \text{ mA}$	V_F		1.2	1.4	V
Reverse voltage	$I_R = 10 \text{ μA}$	V_R	10			V
Radiant power ¹	$I_F = 100 \text{ mA}$	Φ_e	0.75	1.5		mW
Radiant power ²	$I_F = 100 \text{ mA}$	Φ_e		3.0		mW
Peak wavelength	$I_F = 100 \text{ mA}$	λ_p	1000	1020	1050	nm
Spectral bandwidth at 50%	$I_F = 100 \text{ mA}$	$\Delta\lambda_{0.5}$		80		nm
Switching time	$I_F = 100 \text{ mA}$	t_r, t_f		10		ns

¹Measured on bare chip on TO-18 header with *EPIGAP* equipment

²Measured on epoxy covered chip on TO-18 header with *EPIGAP* equipment

Labeling

Type	Lot N°	$\Phi_e(\text{typ})$ [mW]	$V_F(\text{typ})$ [V]	Quantity
ELC-1020-28-1				

Packing: Chips on adhesive film with wire-bond side on top